

**60V PNP HIGH PERFORMANCE TRANSISTOR IN SOT223**

**Description**

This Bipolar Junction Transistor (BJT) is designed to meet the stringent requirements of automotive applications.

**Features**

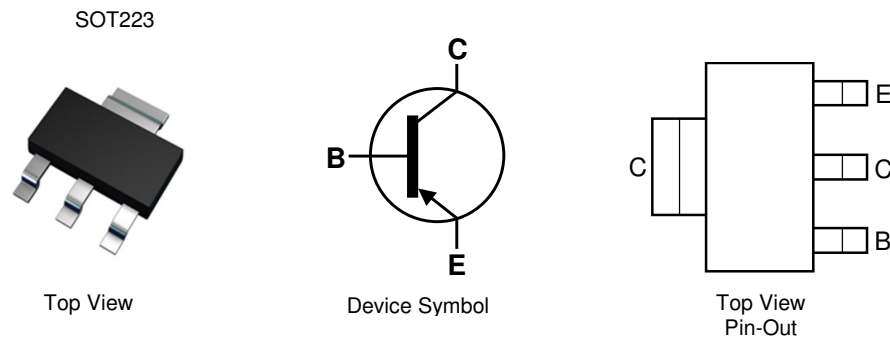
- $BV_{CE0} > -60V$
- $I_C = -3A$  High Continuous Current
- $I_{CM} = -6A$  Peak Pulse Current
- Low Saturation Voltage  $V_{CE(sat)} < -300mV @ -1A$
- Complementary NPN Type: FZT651Q
- **Lead-Free Finish; RoHS Compliant (Notes 1 & 2)**
- **Halogen and Antimony Free. "Green" Device (Note 3)**
- **Qualified to AEC-Q101 Standards for High Reliability**
- **PPAP Capable (Note 4)**

**Applications**

- Automotive Lighting
- MOSFET and IGBT Gate Driving

**Mechanical Data**

- Case: SOT223
- Case Material: Molded Plastic. "Green" Molding Compound. UL Flammability Rating 94V-0
- Moisture Sensitivity: Level 1 per J-STD-020
- Terminals: Finish - Matte Tin Plated Leads. Solderable per MIL-STD-202, Method 208 @3
- Weight: 0.112 grams (Approximate)

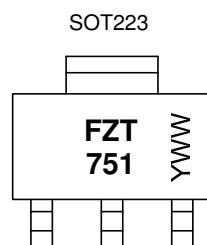


**Ordering Information** (Notes 4 & 5)

Product	Compliance	Marking	Reel size (inches)	Tape width (mm)	Quantity per reel
FZT751QTA	Automotive	FZT751	7	12	1,000
FZT751QTC	Automotive	FZT751	13	12	4,000

- Notes:
1. EU Directive 2002/95/EC (RoHS) & 2011/65/EU (RoHS 2) compliant. All applicable RoHS exemptions applied.
  2. See [http://www.diodes.com/quality/lead\\_free.html](http://www.diodes.com/quality/lead_free.html) for more information about Diodes Incorporated's definitions of Halogen- and Antimony-free, "Green" and Lead-free.
  3. Halogen- and Antimony-free "Green" products are defined as those which contain <900ppm bromine, <900ppm chlorine (<1500ppm total Br + Cl) and <1000ppm antimony compounds.
  4. Automotive products are AEC-Q101 qualified and are PPAP capable. Automotive, AEC-Q101 and standard products are electrically and thermally the same, except where specified. For more information, please refer to [http://www.diodes.com/quality/product\\_compliance\\_definitions/](http://www.diodes.com/quality/product_compliance_definitions/).
  5. For packaging details, go to our website at <http://www.diodes.com/products/packages.html>.

**Marking Information**



FZT 751 = Product Type Marking Code  
 YWW = Date Code Marking  
 Y or  $\bar{Y}$  = Last Digit of Year (ex: 5= 2015)  
 WW or  $\bar{W}W$  = Week Code (01~53)

### Absolute Maximum Ratings (@ $T_A = +25^\circ\text{C}$ , unless otherwise specified.)

Characteristic	Symbol	Value	Unit
Collector-Base Voltage	$V_{CBO}$	-80	V
Collector-Emitter Voltage	$V_{CEO}$	-60	V
Emitter-Base Voltage	$V_{EBO}$	-7	V
Continuous Collector Current	$I_C$	-3	A
Peak Pulse Current	$I_{CM}$	-6	A

### Thermal Characteristics (@ $T_A = +25^\circ\text{C}$ , unless otherwise specified.)

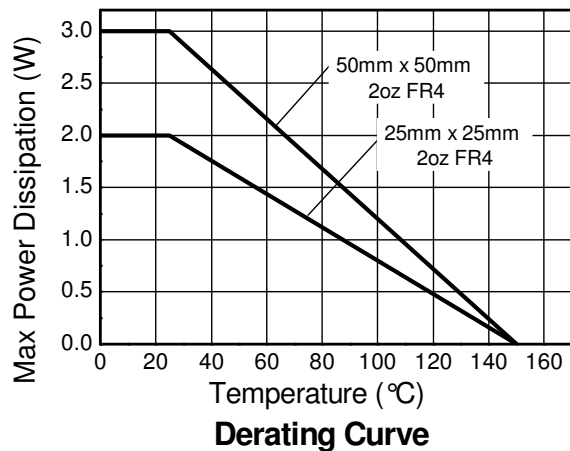
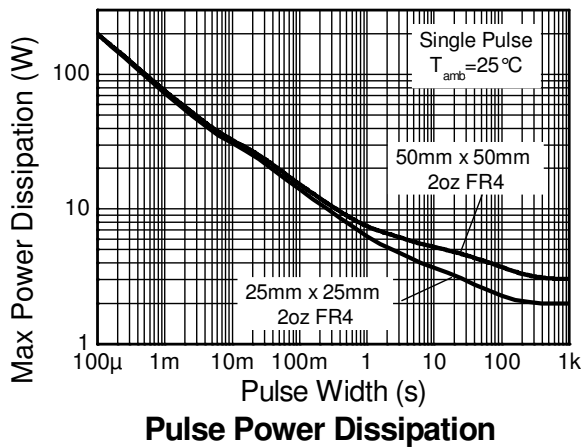
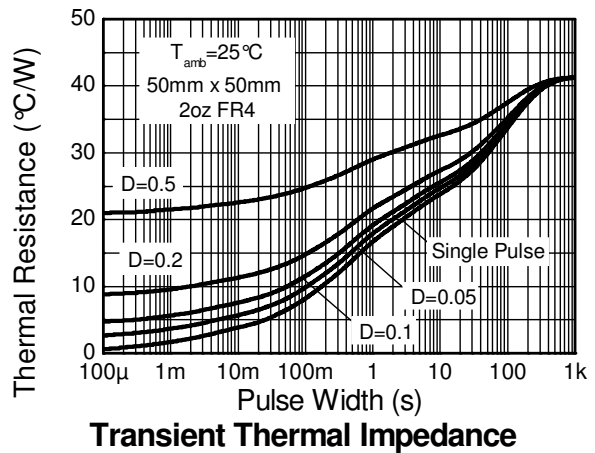
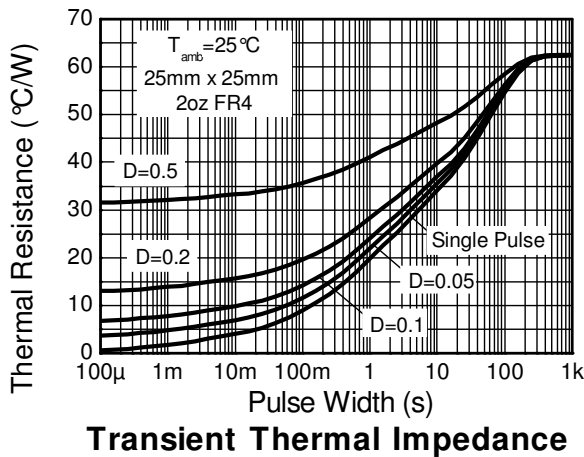
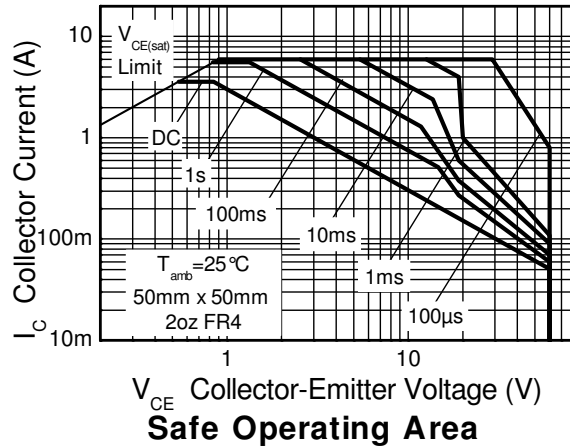
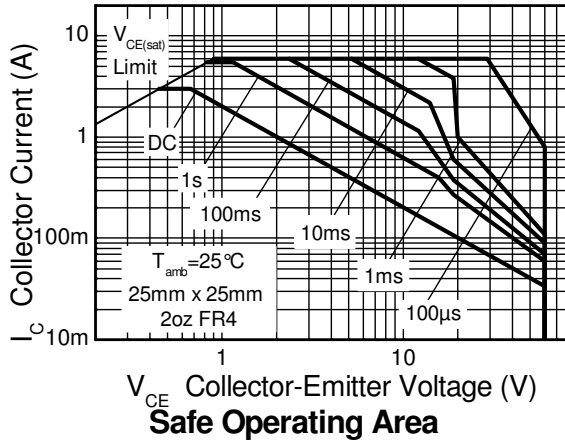
Characteristic	Symbol	Value	Unit
Power Dissipation	$P_D$	2	W
		3	W
Thermal Resistance, Junction to Ambient	$R_{\theta JA}$	62.5	$^\circ\text{C/W}$
		41.7	$^\circ\text{C/W}$
Thermal Resistance, Junction to Leads	$R_{\theta JL}$	12.9	$^\circ\text{C/W}$
Operating and Storage Temperature Range	$T_J, T_{STG}$	-55 to +150	$^\circ\text{C}$

### ESD Ratings (Note 9)

Characteristic	Symbol	Value	Unit	JEDEC Class
Electrostatic Discharge - Human Body Model	ESD HBM	4,000	V	3A
Electrostatic Discharge - Machine Model	ESD MM	400	V	C

- Notes:
6. For a device mounted with the collector lead on 25mm x 25mm 2oz copper that is on a single-sided 1.6mm FR4 PCB; device is measured under still air conditions whilst operating in steady-state.
  7. Same as Note 6, except the device is mounted on 50mm x 50mm 2oz copper.
  8. Thermal resistance from junction to solder-point (at the end of the collector lead).
  9. Refer to JEDEC specification JESD22-A114 and JESD22-A115.

**Thermal Characteristics and Derating Information**

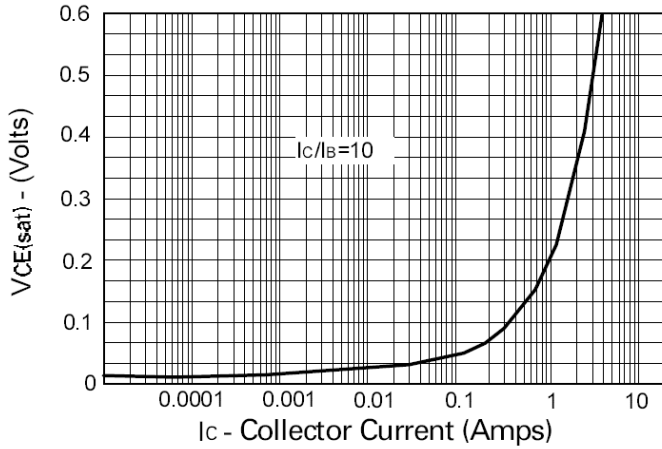


**Electrical Characteristics** (@T<sub>A</sub> = +25 °C, unless otherwise specified.)

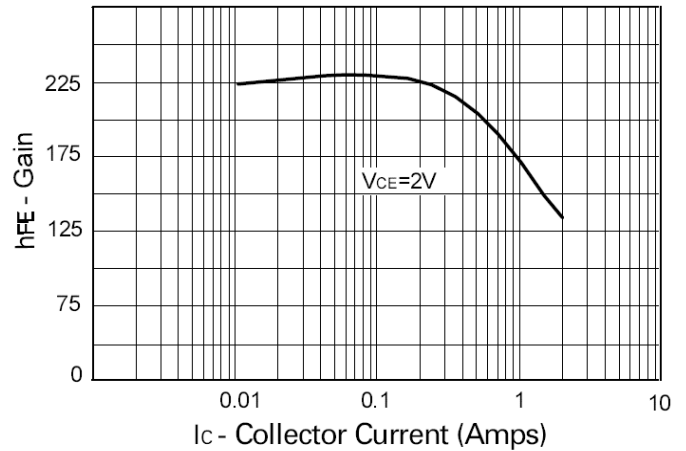
Characteristic	Symbol	Min	Typ	Max	Unit	Test Condition
Collector-Base Breakdown Voltage	BV <sub>CBO</sub>	-80	-	-	V	I <sub>C</sub> = -100μA
Collector-Emitter Breakdown Voltage (Note 10)	BV <sub>CEO</sub>	-60	-	-	V	I <sub>C</sub> = -10mA
Emitter-Base Breakdown Voltage	BV <sub>EBO</sub>	-7	-	-	V	I <sub>E</sub> = -100μA
Collector Cut-off Current	I <sub>CBO</sub>	-	<1	-100	nA	V <sub>CB</sub> = -60V
		-	-	-10	μA	V <sub>CB</sub> = -60V, T <sub>amb</sub> = +100 °C
Emitter Cut-off Current	I <sub>EBO</sub>	-	<1	-100	nA	V <sub>EB</sub> = -4V
Collector-Emitter Saturation Voltage (Note 10)	V <sub>CE(sat)</sub>	-	-0.15	-0.3	V	I <sub>C</sub> = -1A, I <sub>B</sub> = -100mA
		-	-0.45	-0.6		I <sub>C</sub> = -3A, I <sub>B</sub> = -300mA
Base-Emitter Saturation Voltage (Note 10)	V <sub>BE(sat)</sub>	-	-0.9	-1.25	V	I <sub>C</sub> = -1A, I <sub>B</sub> = -100mA
Base-Emitter Turn-On Voltage (Note 10)	V <sub>BE(on)</sub>	-	-0.8	-1.0	V	I <sub>C</sub> = -1A, V <sub>CE</sub> = -2V
DC Current Gain (Note 10)	h <sub>FE</sub>	70	200	-	-	I <sub>C</sub> = -50mA, V <sub>CE</sub> = -2V
		100	200	300		I <sub>C</sub> = -500mA, V <sub>CE</sub> = -2V
		80	170	-		I <sub>C</sub> = -1A, V <sub>CE</sub> = -2V
		40	150	-		I <sub>C</sub> = -2A, V <sub>CE</sub> = -2V
Current Gain-Bandwidth Product	f <sub>T</sub>	100	140	-	MHz	V <sub>CE</sub> = -5V, I <sub>C</sub> = -100mA f = 100MHz
Turn-On Time	t <sub>on</sub>	-	40	-	ns	V <sub>CC</sub> = -10V, I <sub>C</sub> = -500mA
Turn-Off Time	t <sub>off</sub>	-	450	-	ns	I <sub>B1</sub> = I <sub>B2</sub> = -50mA
Output Capacitance	C <sub>obo</sub>	-	-	30	pF	V <sub>CB</sub> = -10V, f = 1MHz

Note: 10. Measured under pulsed conditions. Pulse width ≤ 300 μs. Duty cycle ≤ 2%.

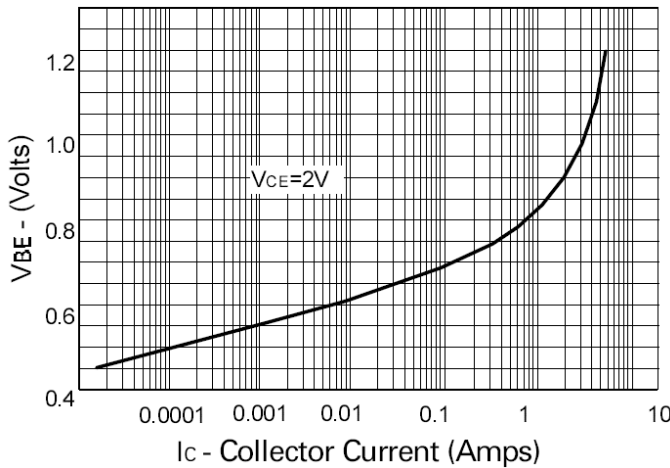
**Typical Electrical Characteristics** (@ $T_A = +25^\circ\text{C}$ , unless otherwise specified.)



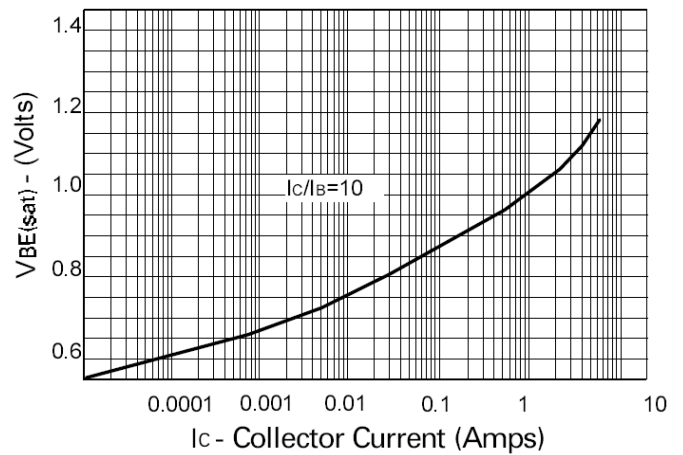
**$V_{CE(sat)} v I_C$**



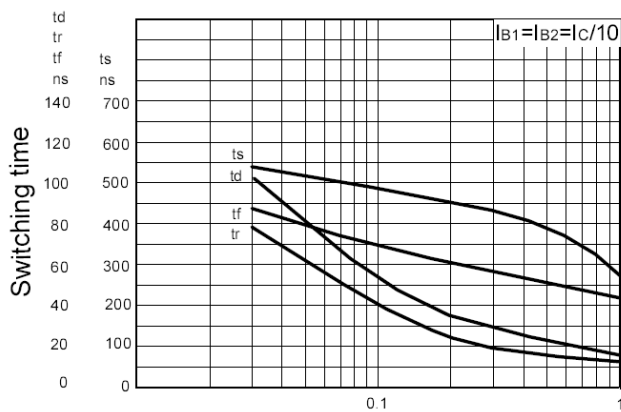
**$hFE v I_C$**



**$V_{BE(on)} v I_C$**



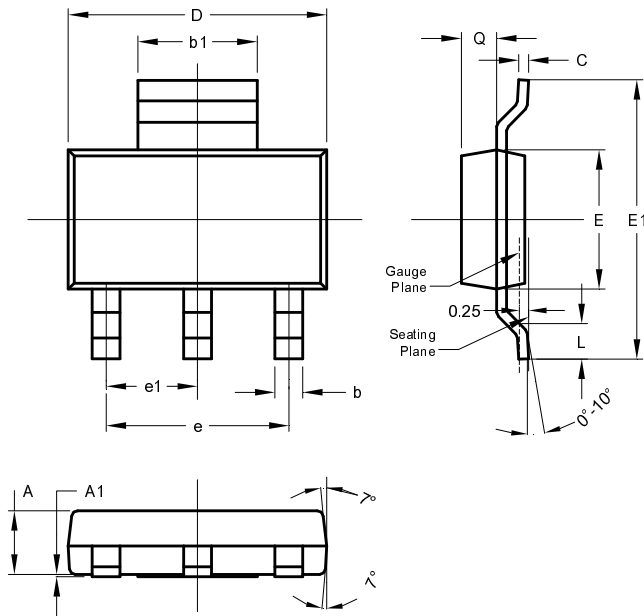
**$V_{BE(sat)} v I_C$**



**Switching Speeds**

## Package Outline Dimensions

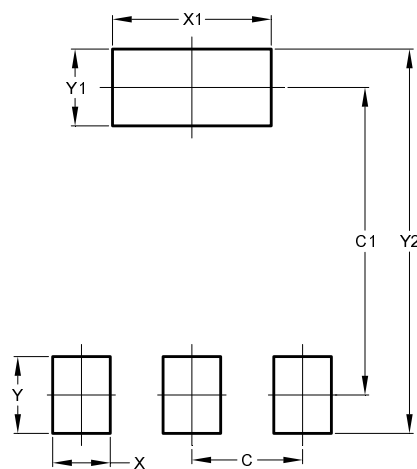
Please see AP02002 at <http://www.diodes.com/datasheets/ap02002.pdf> for the latest version.



SOT223			
Dim	Min	Max	Typ
A	1.55	1.65	1.60
A1	0.010	0.15	0.05
b	20.60	30.80	0.70
b1	2.90	3.10	03.00
C	0.20	0.30	0.25
D	6.45	6.55	6.50
E	3.45	3.55	3.50
E1	6.90	7.10	7.00
e	—	—	4.60
e1	—	—	2.30
L	0.85	1.05	0.95
Q	0.84	0.94	0.89
All Dimensions in mm			

## Suggested Pad Layout

Please see AP02001 at <http://www.diodes.com/datasheets/ap02001.pdf> for the latest version.



Dimensions	Value (in mm)
C	2.30
C1	6.40
X	1.20
X1	3.30
Y	1.60
Y1	1.60
Y2	8.00

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